

SIPMOS® Small-Signal-Transistor

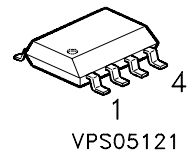
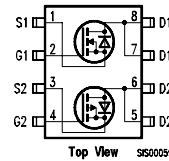
Features

- Dual N- and P -Channel
- Enhancement mode
- Logic Level
- Avalanche rated
- Pb-free lead plating; RoHS compliant



Product Summary

		N	P	
Drain source voltage	V_{DS}	60	-60	V
Drain-Source on-state resistance	$R_{DS(on)}$	0.11	0.3	Ω
Continuous drain current	I_D	3.1	-2	A



Type	Package	Marking
BSO 615 C	PG-DSO-8	615C

Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value		Unit
		N	P	
Continuous drain current $T_A = 25\text{ °C}$ $T_A = 70\text{ °C}$	I_D	3.1 2.5	-2 -1.6	A
Pulsed drain current $T_A = 25\text{ °C}$	$I_{D\text{ puls}}$	12.4	-8	
Avalanche energy, single pulse $I_D = 3.1\text{ A}$, $V_{DD} = 25\text{ V}$, $R_{GS} = 25\text{ }\Omega$ $I_D = -2\text{ A}$, $V_{DD} = -25\text{ V}$, $R_{GS} = 25\text{ }\Omega$	E_{AS}	47 -	- 70	mJ
Avalanche energy, periodic limited by $T_{j\text{max}}$	E_{AR}	0.2	0.2	
Reverse diode dv/dt , $T_{j\text{max}} = 150\text{ °C}$ $I_S = 3.1\text{ A}$, $V_{DS} = 48\text{ V}$, $di/dt = 200\text{ A}/\mu\text{s}$ $I_S = -2\text{ A}$, $V_{DS} = -48\text{ V}$, $di/dt = -200\text{ A}/\mu\text{s}$	dv/dt	6 -	- 6	kV/ μs
Gate source voltage	V_{GS}	± 20	± 20	V
Power dissipation $T_A = 25\text{ °C}$	P_{tot}	2	2	W
Operating and storage temperature	T_j, T_{stg}	-55...+150		°C
IEC climatic category; DIN IEC 68-1		55/150/56		

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Dynamic Characteristics

Thermal resistance, junction - soldering point (Pin 4)	N	R_{thJS}	-	-	40	K/W
	P		-	-	40	
SMD version, device on PCB: @ min. footprint; $t \leq 10$ sec. @ 6 cm ² cooling area ¹⁾ ; $t \leq 10$ sec. @ min. footprint; $t \leq 10$ sec. @ 6 cm ² cooling area ¹⁾ ; $t \leq 10$ sec.	N	R_{thJA}	-	-	100	
	N		-	-	62.5	
	P		-	-	110	
	P		-	-	62.5	

Static Characteristics, at $T_j = 25$ °C, unless otherwise specified

Drain- source breakdown voltage $V_{GS} = 0$ V, $I_D = 250$ μ A $V_{GS} = 0$ V, $I_D = -250$ μ A	N	$V_{(BR)DSS}$	60	-	-	V
	P		-60	-	-	
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 20$ μ A $I_D = -450$ μ A	N	$V_{GS(th)}$	1.2	1.6	2.0	
	P		-1	-1.5	-2.0	
Zero gate voltage drain current $V_{DS} = 60$ V, $V_{GS} = 0$ V, $T_j = 25$ °C $V_{DS} = 60$ V, $V_{GS} = 0$ V, $T_j = 125$ °C $V_{DS} = -60$ V, $V_{GS} = 0$ V, $T_j = 25$ °C $V_{DS} = -60$ V, $V_{GS} = 0$ V, $T_j = 125$ °C	N	I_{DSS}	-	0.1	1	μ A
	N		-	10	100	
	P		-	-0.1	-1	
	P		-	-10	-100	
Gate-source leakage current $V_{GS} = 20$ V, $V_{DS} = 0$ V $V_{GS} = -20$ V, $V_{DS} = 0$ V	N	I_{GSS}	-	10	100	nA
	P		-	-10	-100	
Drain-source on-state resistance $V_{GS} = 4.5$ V, $I_D = 2.7$ A $V_{GS} = -4.5$ V, $I_D = -1.7$ A	N	$R_{DS(on)}$	-	0.1	0.15	Ω
	P		-	0.27	0.45	
Drain-source on-state resistance $V_{GS} = 10$ V, $I_D = 3.1$ A $V_{GS} = -10$ V, $I_D = -2$ A	N	$R_{DS(on)}$	-	0.07	0.11	
	P		-	0.19	0.3	

¹Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μ m thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

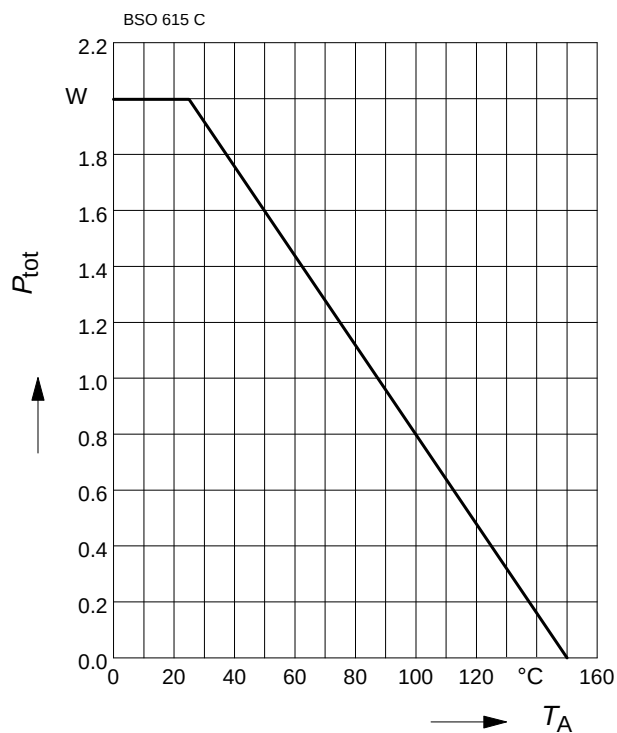
Parameter		Symbol	Values			Unit
			min.	typ.	max.	
Characteristics						
Transconductance		g_{fs}				S
$V_{DS} \geq 2 * I_D * R_{DS(on)max}, I_D = 2.7\text{ A}$	N		2.25	5.5	-	
$V_{VDS} \geq 2 * I_D * R_{DS(on)max}, I_D = -1.7\text{ A}$	P		1.2	2.4	-	
Input capacitance		C_{iss}				pF
$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N		-	300	380	
$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1\text{ MHz}$	P		-	365	460	
Output capacitance		C_{oss}				
$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N		-	90	120	
$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1\text{ MHz}$	P		-	105	135	
Reverse transfer capacitance		C_{rss}				
$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N		-	50	65	
$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1\text{ MHz}$	P		-	40	50	
Turn-on delay time		$t_{d(on)}$				ns
$V_{DD} = 30\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 2.7\text{ A}, R_G = 16\text{ }\Omega$	N		-	16	24	
$V_{DD} = -30\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -1.7\text{ A}, R_G = 13\text{ }\Omega$	P		-	24	36	
Rise time		t_r				
$V_{DD} = 30\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 2.7\text{ A}, R_G = 16\text{ }\Omega$	N		-	75	115	
$V_{DD} = -30\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -1.7\text{ A}, R_G = 13\text{ }\Omega$	P		-	105	160	
Turn-off delay time		$t_{d(off)}$				
$V_{DD} = 30\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 2.7\text{ A}, R_G = 16\text{ }\Omega$	N		-	25	40	
$V_{DD} = -30\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -1.7\text{ A}, R_G = 13\text{ }\Omega$	P		-	125	190	
Fall time		t_f				
$V_{DD} = 30\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 2.7\text{ A}, R_G = 16\text{ }\Omega$	N		-	18	27	
$V_{DD} = -30\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -1.7\text{ A}, R_G = 13\text{ }\Omega$	P		-	90	135	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter		Symbol	Values			Unit	
			min.	typ.	max.		
Characteristics							
Gate to source charge $V_{DD} = 48\text{ V}$, $I_D = 3.1\text{ A}$ $V_{DD} = -48\text{ V}$, $I_D = -2\text{ A}$	N P	Q_{gs}	- -	0.5 1.7	0.75 2.6	nC	
Gate to drain charge $V_{DD} = 48\text{ V}$, $I_D = 3.1\text{ A}$ $V_{DD} = -48\text{ V}$, $I_D = -2\text{ A}$	N P	Q_{gd}	- -	6.3 4.3	9.5 6.5		
Gate charge total $V_{DD} = 48\text{ V}$, $I_D = 3.1\text{ A}$, $V_{GS} = 0\text{ to }10\text{V}$ $V_{DD} = -48\text{ V}$, $I_D = -2\text{ A}$, $V_{GS} = 0\text{ to }-10\text{V}$	N P	Q_g	- -	15 13.5	22.5 20		
Gate plateau voltage $V_{DD} = 48\text{ V}$, $I_D = 3.1\text{ A}$ $V_{DD} = -48\text{ V}$, $I_D = -2\text{ A}$	N P	$V_{(plateau)}$	- -	3.1 -2.8	- -		V
Reverse Diode							
Inverse diode continuous forward current $T_A = 25\text{ }^{\circ}\text{C}$	N P	I_S	- -	- -	3.1 -2		A
Inverse diode direct current,pulsed $T_A = 25\text{ }^{\circ}\text{C}$	N P	I_{SM}	- -	- -	12.4 -8		
Inverse diode forward voltage $V_{GS} = 0\text{ V}$, $I_F = I_S$ $V_{GS} = 0\text{ V}$, $I_F = I_S$	N P	V_{SD}	- -	0.8 -0.8	1.1 -1.1	V	
Reverse recovery time $V_R = 30\text{ V}$, $I_F{=}I_S$, $di_F/dt = 100\text{ A}/\mu\text{s}$ $V_R = -30\text{ V}$, $I_F{=}I_S$, $di_F/dt = -100\text{ A}/\mu\text{s}$	N P	t_{rr}	- -	50 85	75 130	ns	
Reverse recovery charge $V_R = 30\text{ V}$, $I_F{=}I_S$, $di_F/dt = 100\text{ A}/\mu\text{s}$ $V_R = -30\text{ V}$, $I_F{=}I_S$, $di_F/dt = -100\text{ A}/\mu\text{s}$	N P	Q_{rr}	- -	70 120	105 180	nC	

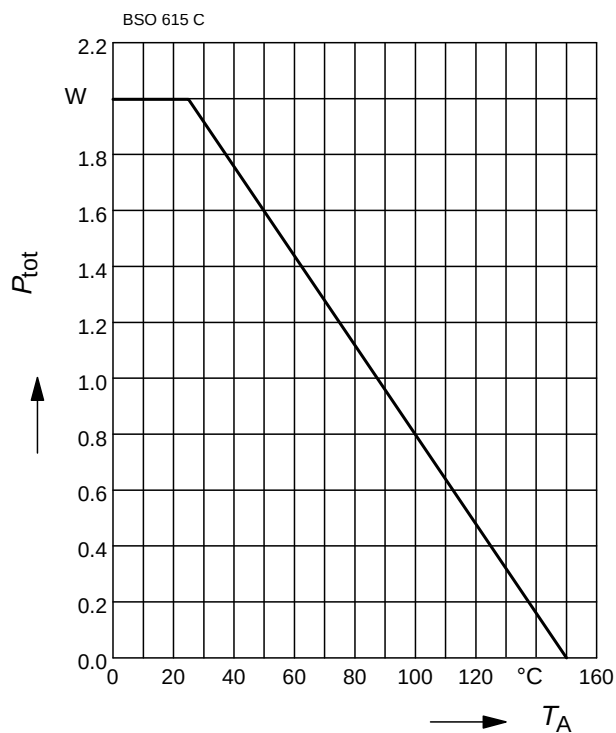
Power Dissipation (N-Ch.)

$$P_{\text{tot}} = f(T_A)$$



Power Dissipation (P-Ch.)

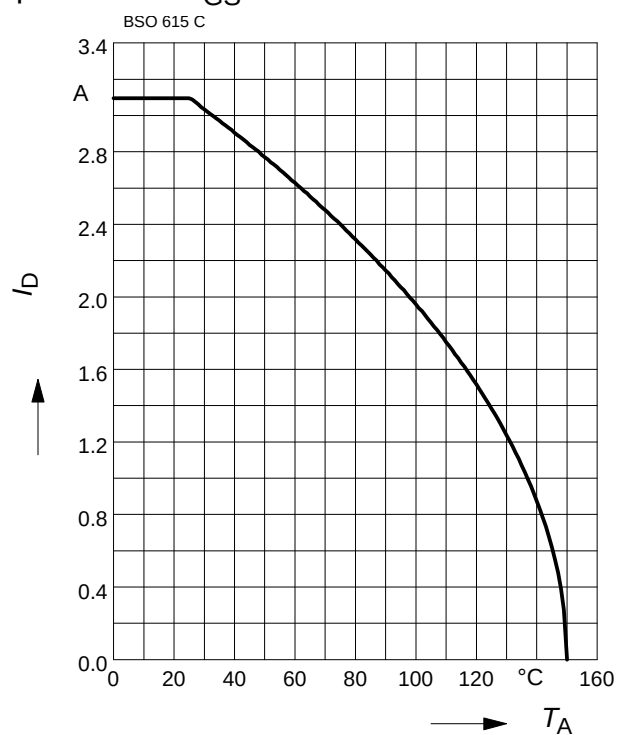
$$P_{\text{tot}} = f(T_A)$$



Drain current (N-Ch.)

$$I_D = f(T_A)$$

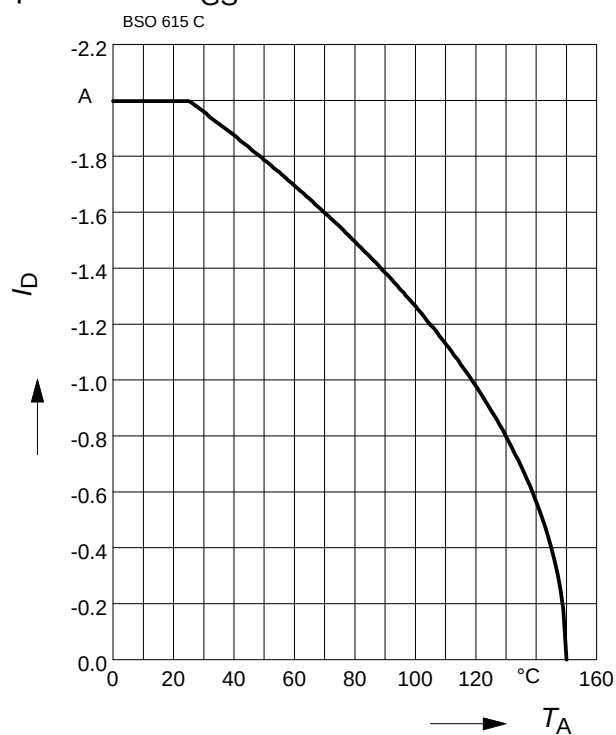
parameter: $V_{GS} \geq 10 \text{ V}$



Drain current (P-Ch.)

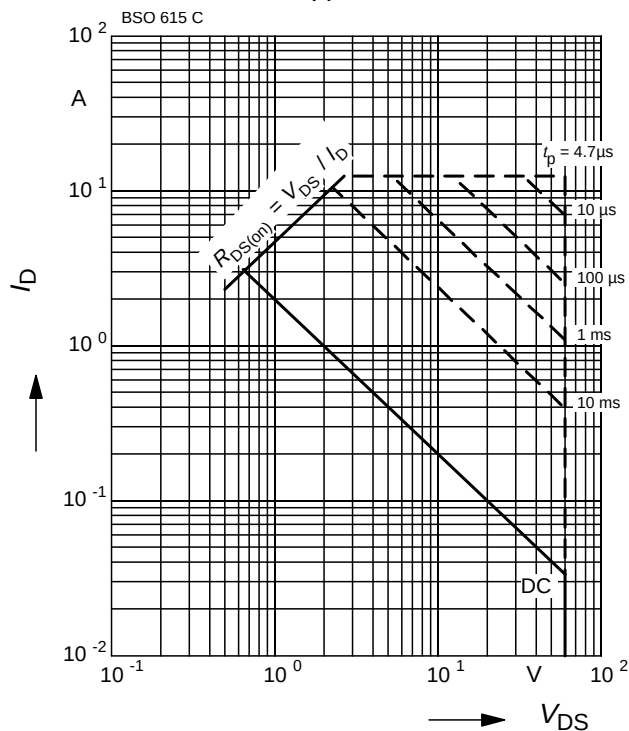
$$I_D = f(T_A)$$

parameter: $V_{GS} \geq -10 \text{ V}$



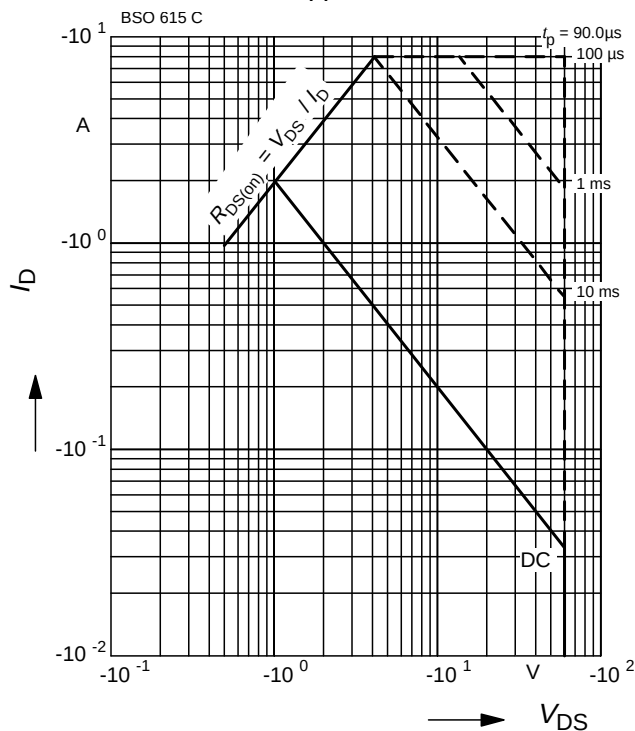
Safe operating area (N-Ch.)

$$I_D = f(V_{DS})$$

parameter : $D = 0$, $T_A = 25\text{ }^{\circ}\text{C}$


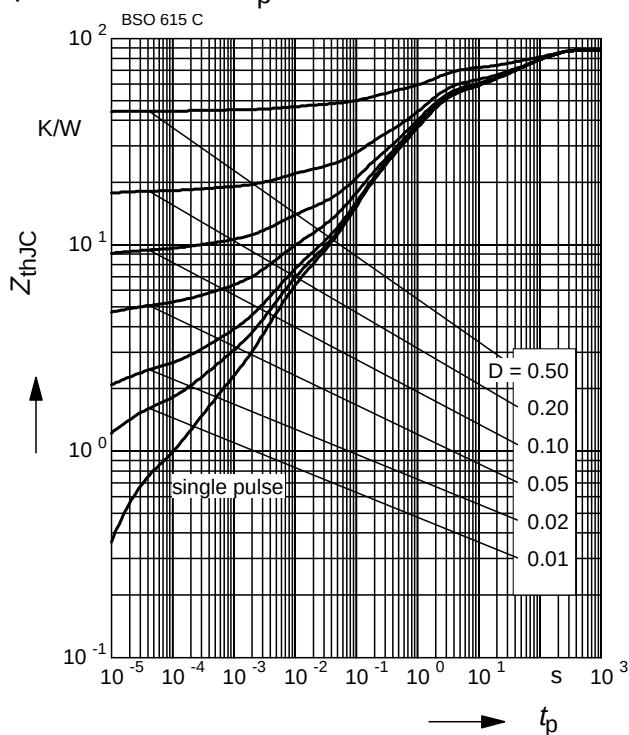
Safe operating area (P-Ch.)

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parameter : $D = 0$, $T_A = 25\text{ }^{\circ}\text{C}$


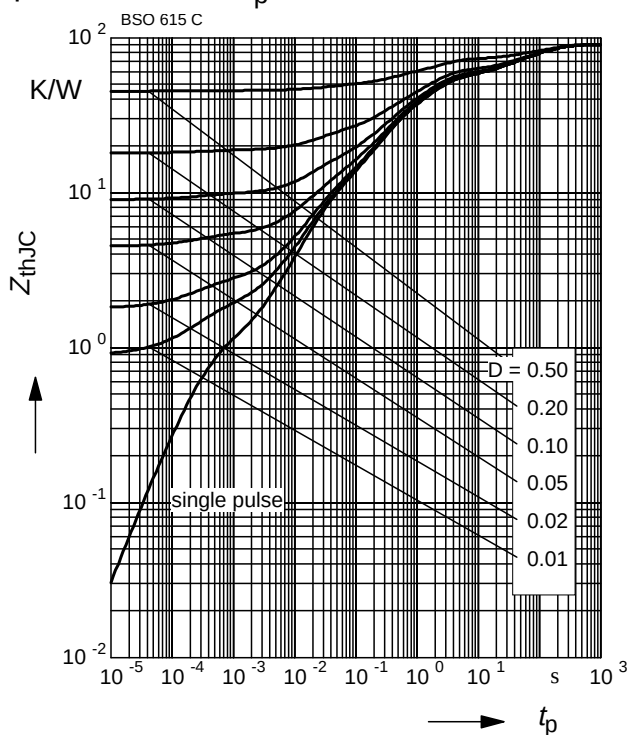
Transient thermal impedance (N-Ch.)

$$Z_{thJC} = f(t_p)$$

parameter : $D = t_p/T$


Transient thermal impedance (P-Ch.)

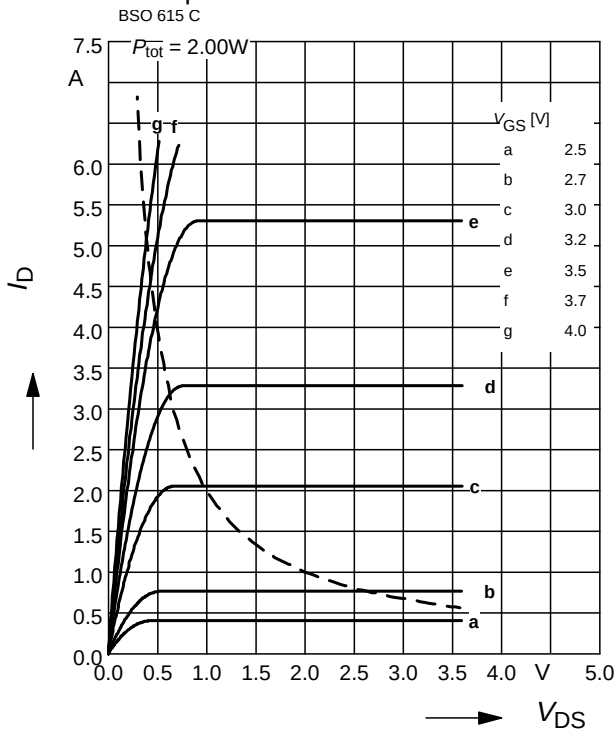
$$Z_{thJC} = f(t_p)$$

parameter : $D = t_p/T$


Typ. output characteristics (N-Ch.)

$$I_D = f(V_{DS})$$

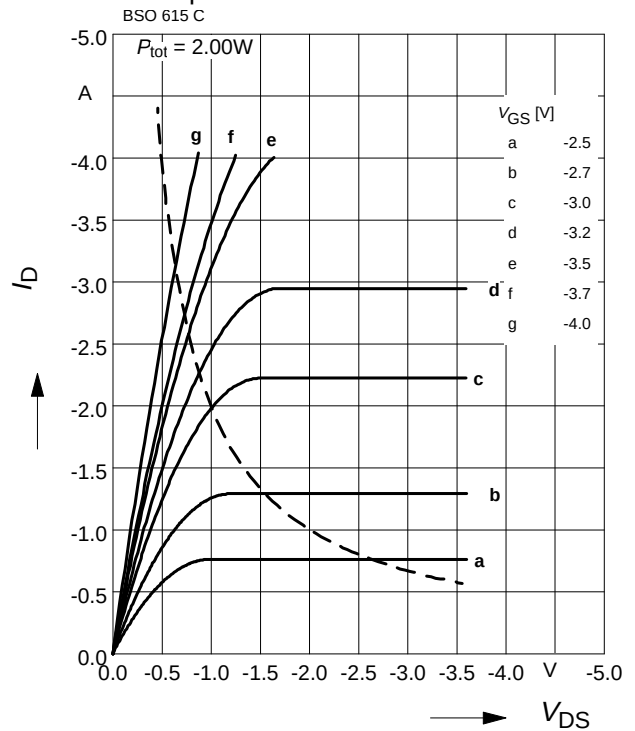
parameter: $t_p = 80 \mu s$



Typ. output characteristics (P-Ch.)

$$I_D = f(V_{DS})$$

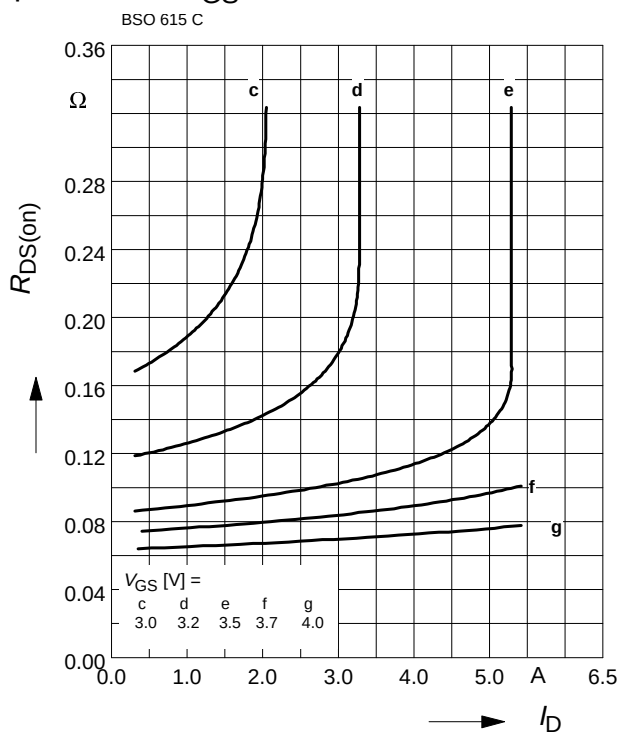
parameter: $t_p = 80 \mu s$



Typ. drain-source-on-resistance (N-Ch.)

$$R_{DS(on)} = f(I_D)$$

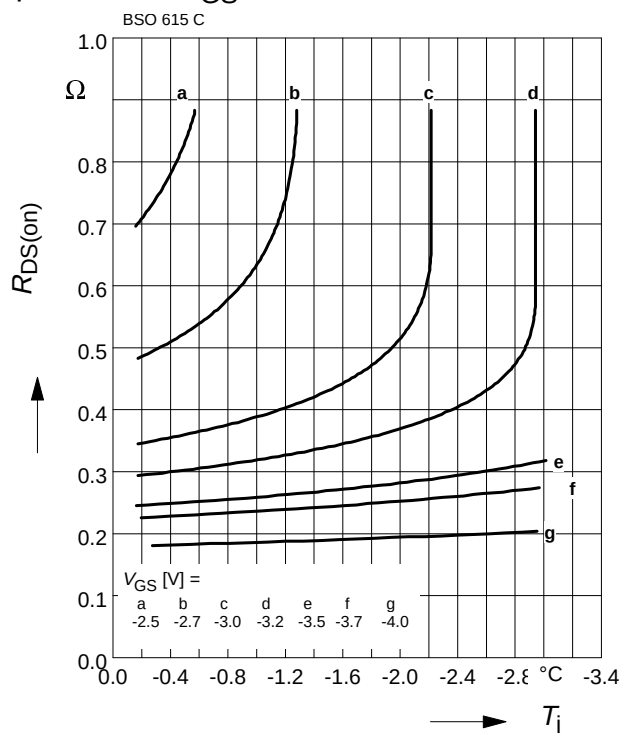
parameter: V_{GS}



Typ. drain-source-on-resistance (P-Ch.)

$$R_{DS(on)} = f(I_D)$$

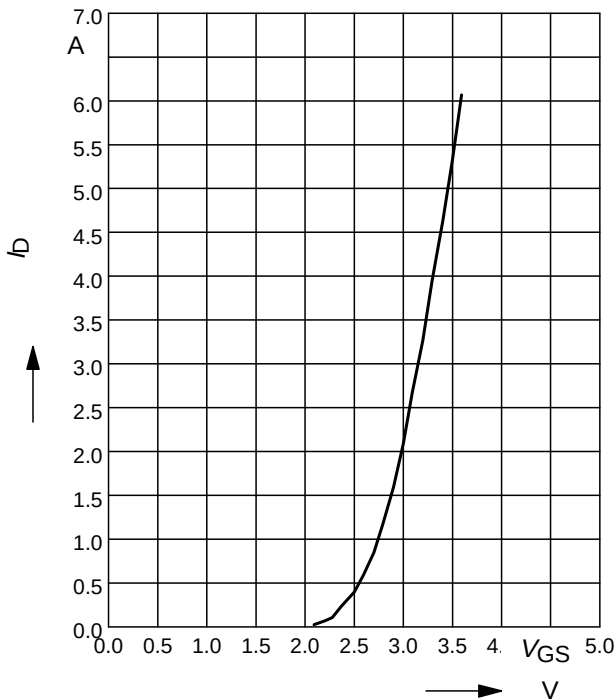
parameter: V_{GS}



Typ. transfer characteristics (N-Ch.)

parameter: $t_p = 80 \mu s$

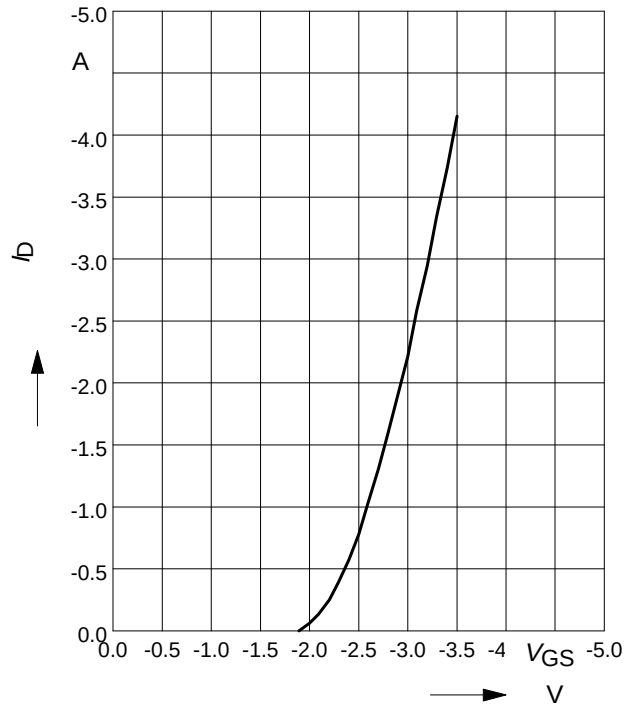
$I_D = f(V_{GS}), V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$



Typ. transfer characteristics (P-Ch.)

parameter: $t_p = 80 \mu s$

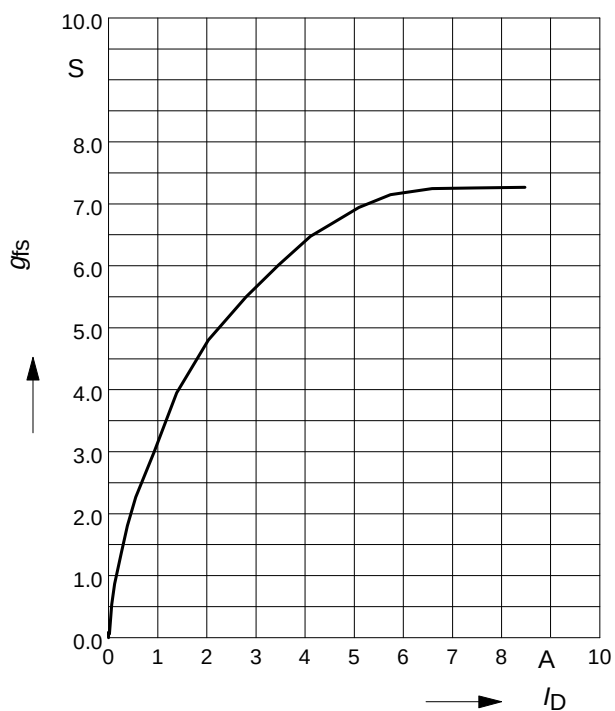
$I_D = f(V_{GS}), V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$



Typ. forward transconductance (N-Ch.)

$g_{fs} = f(I_D); T_j = 25^\circ C$

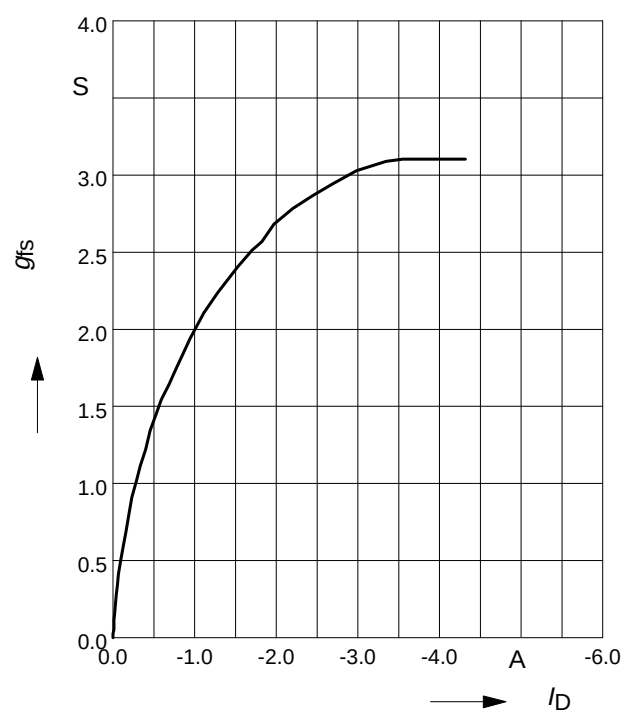
parameter: g_{fs}



Typ. forward transconductance (P-Ch.)

$g_{fs} = f(I_D); T_j = 25^\circ C$

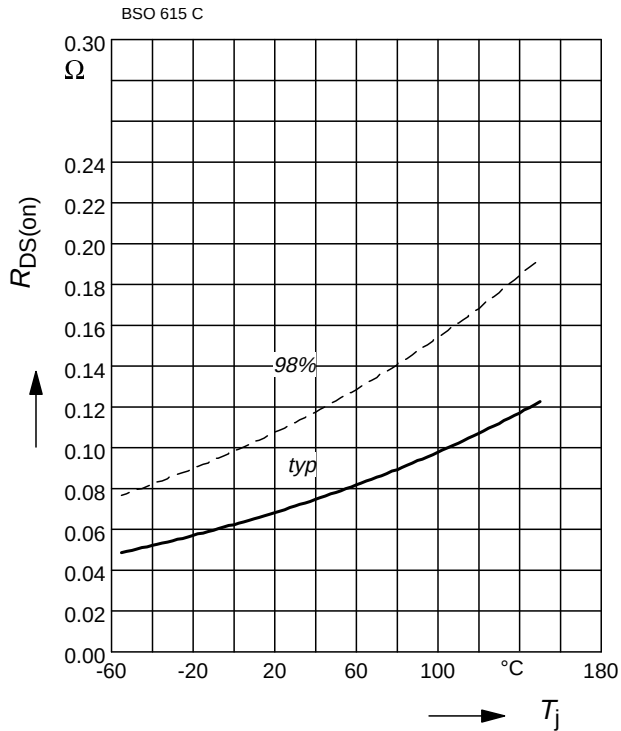
parameter: g_{fs}



Drain-source on-resistance (N-Ch.)

$$R_{DS(on)} = f(T_j)$$

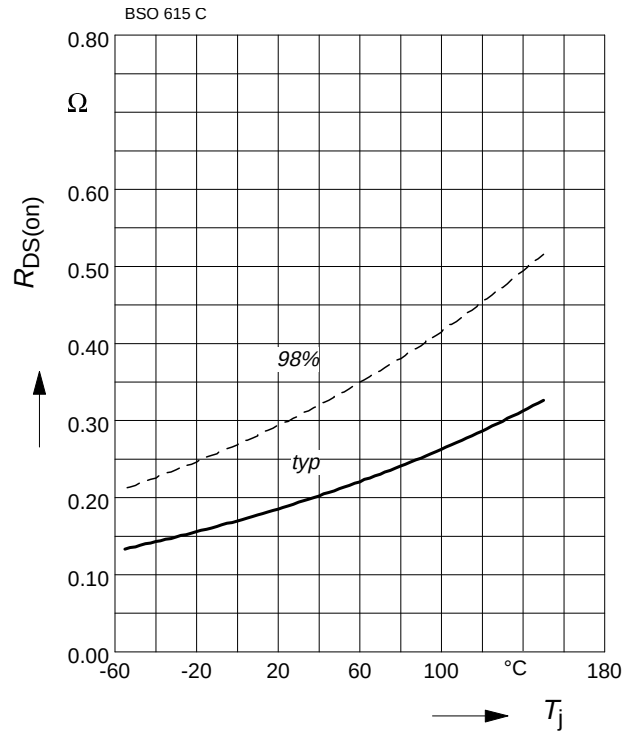
parameter: $I_D = 3.1 \text{ A}$, $V_{GS} = 10 \text{ V}$



Drain-source on-resistance (P-Ch.)

$$R_{DS(on)} = f(T_j)$$

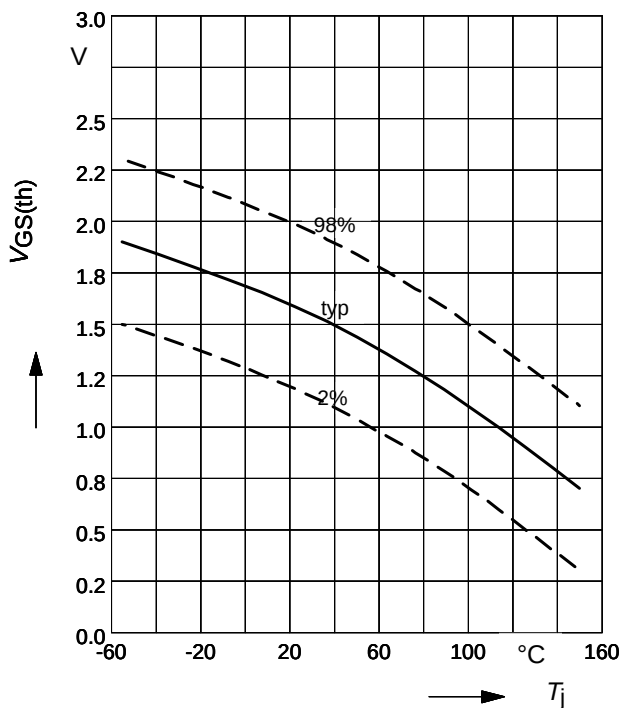
parameter: $I_D = -2 \text{ A}$, $V_{GS} = -10 \text{ V}$



Gate threshold voltage (N-Ch.)

$$V_{GS(th)} = f(T_j)$$

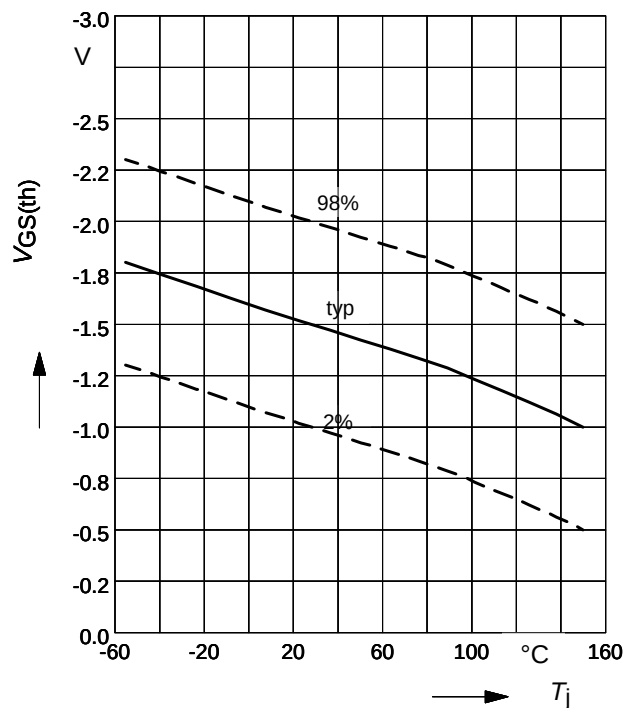
parameter: $V_{GS} = V_{DS}$, $I_D = 20 \mu\text{A}$



Gate threshold voltage (P-Ch.)

$$V_{GS(th)} = f(T_j)$$

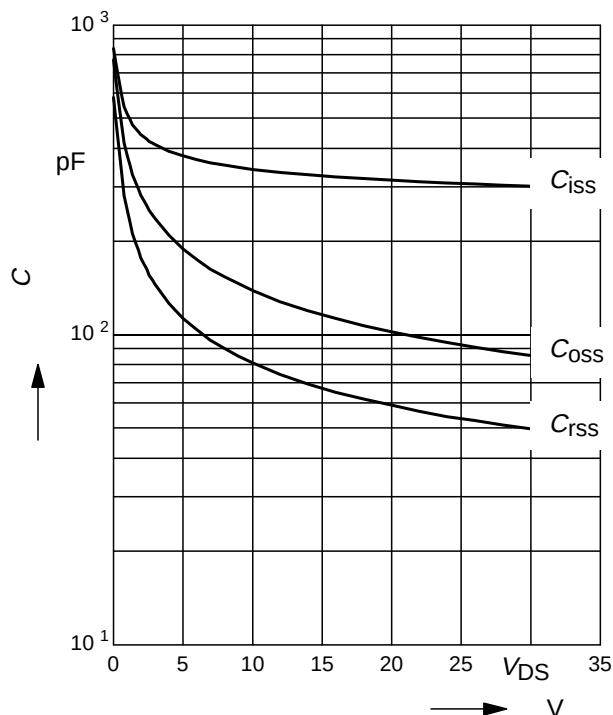
parameter: $V_{GS} = V_{DS}$, $I_D = -450 \mu\text{A}$



Typ. capacitances (N-Ch.)

$$C = f(V_{DS})$$

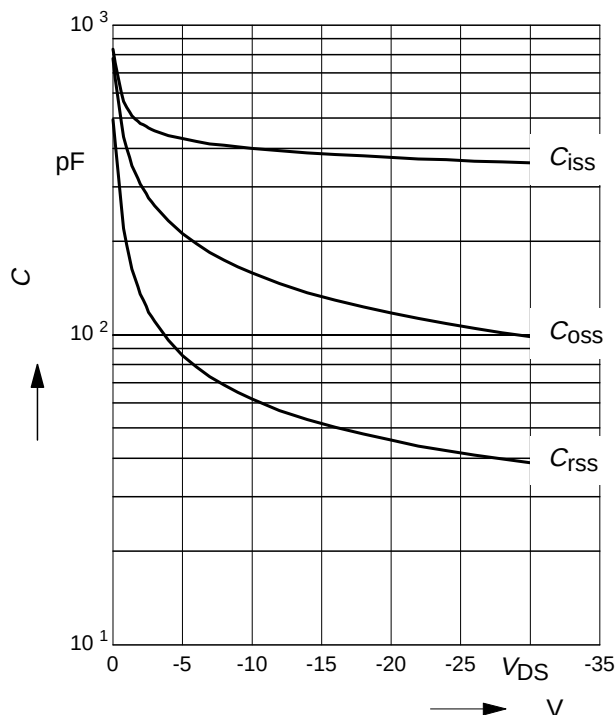
parameter: $V_{GS}=0\text{ V}$, $f=1\text{ MHz}$



Typ. capacitances (P-Ch.)

$$C = f(V_{DS})$$

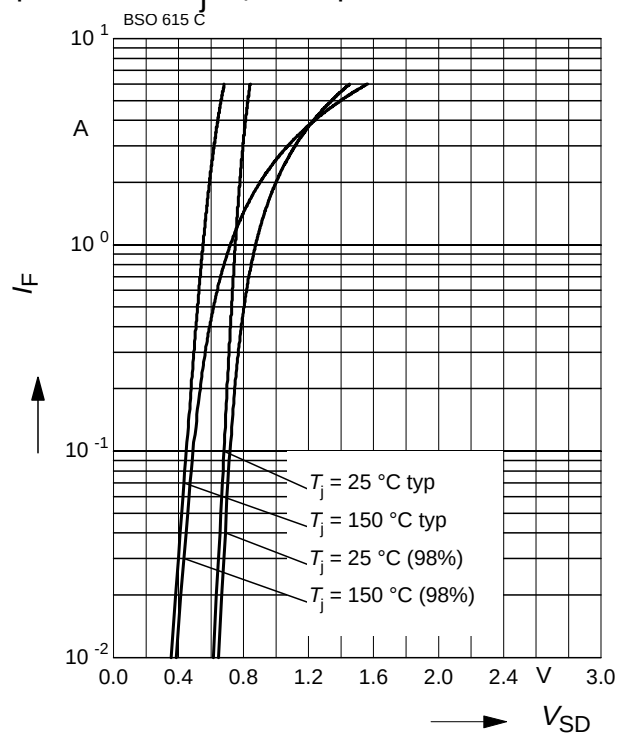
parameter: $V_{GS}=0\text{ V}$, $f=1\text{ MHz}$



Forward characteristics of reverse diode

$$I_F = f(V_{SD}), (\text{N-Ch.})$$

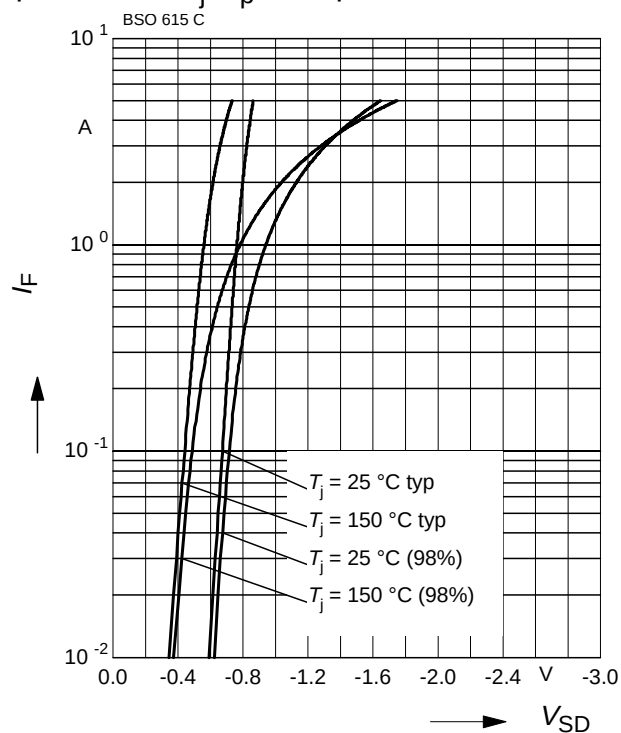
parameter: T_j , $t_p = 80\text{ }\mu\text{s}$



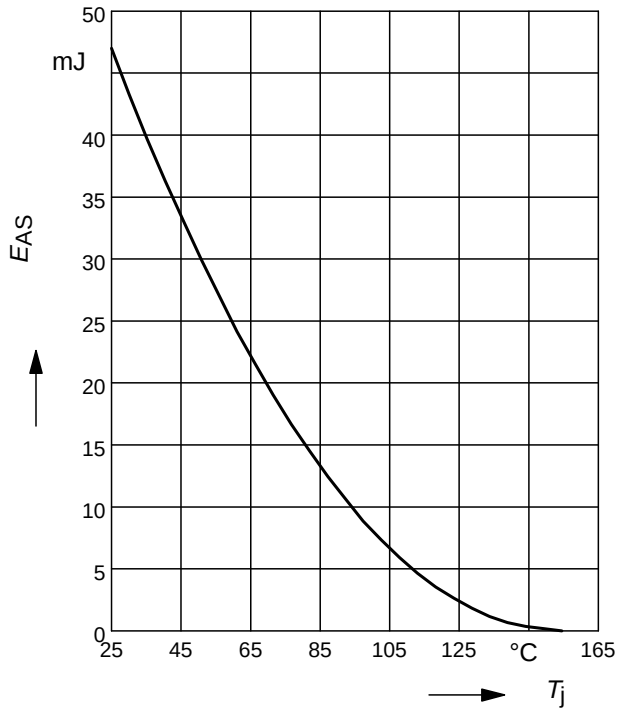
Forward characteristics of reverse diode

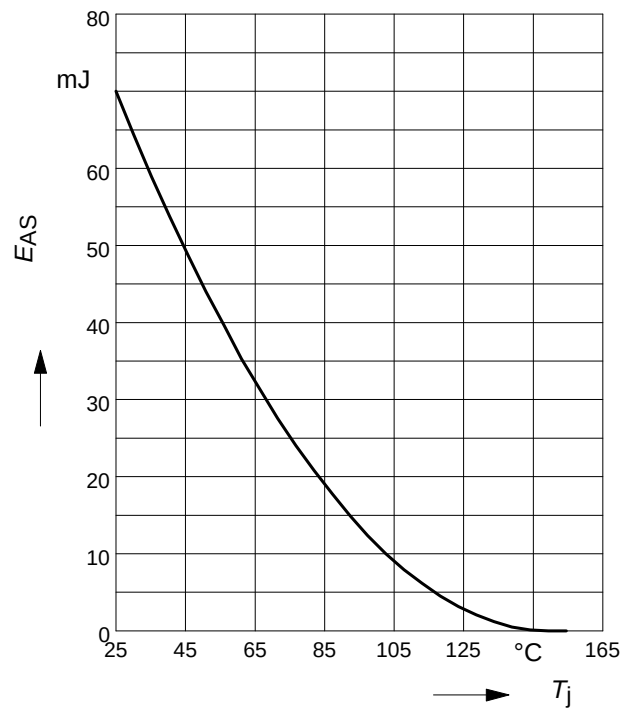
$$I_F = f(V_{SD}), (\text{P-Ch.})$$

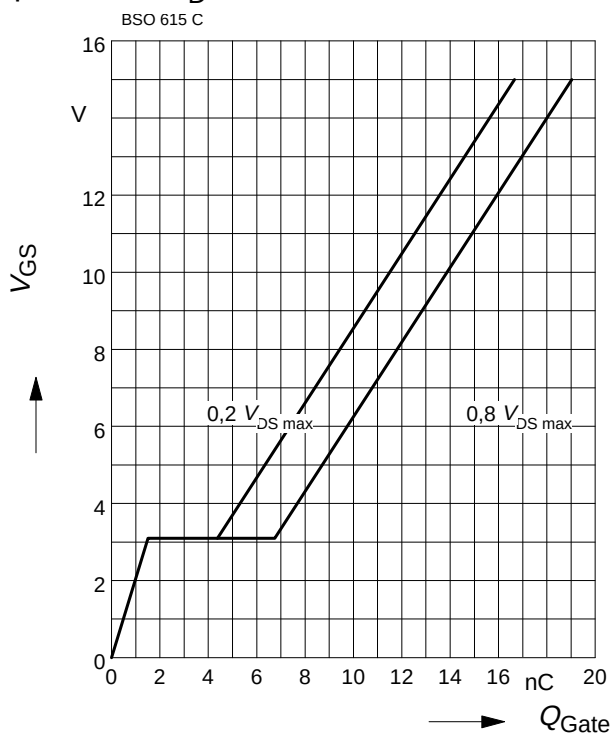
parameter: T_j , $t_p = 80\text{ }\mu\text{s}$

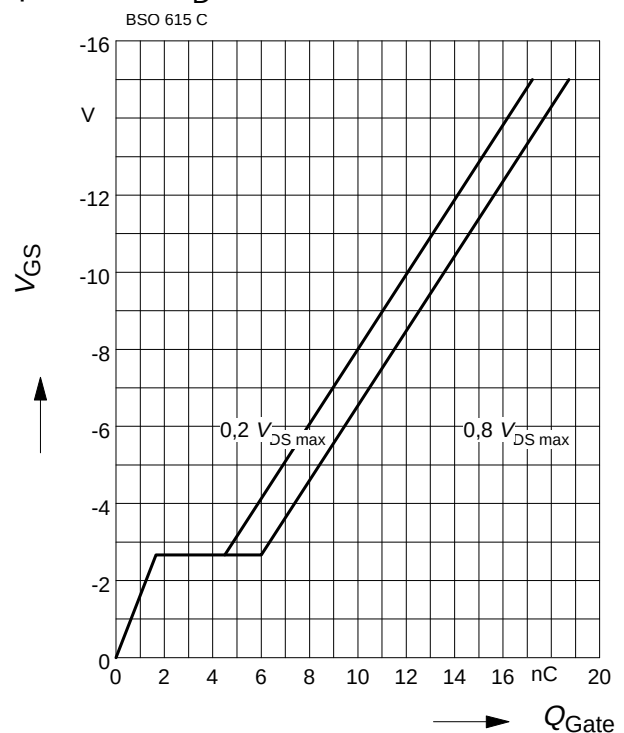


Avalanche Energy $E_{AS} = f(T_j)$ (N-Ch.)

parameter: $I_D = 3.1 \text{ A}$, $V_{DD} = 25 \text{ V}$
 $R_{GS} = 25 \text{ } \Omega$

Avalanche Energy $E_{AS} = f(T_j)$

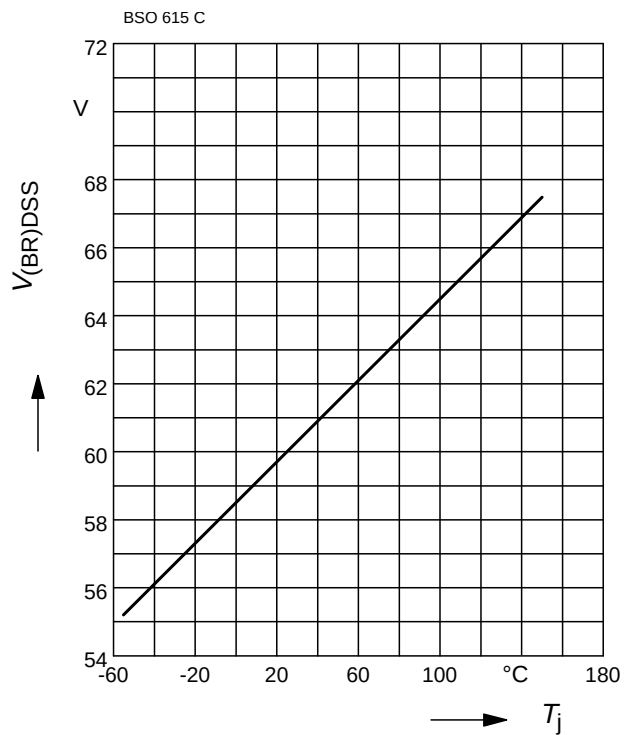
parameter: $I_D = -2 \text{ A}$, $V_{DD} = -25 \text{ V}$
 $R_{GS} = 25 \text{ } \Omega$

Typ. gate charge (N-Ch.)
 $V_{GS} = f(Q_{Gate})$

parameter: $I_D = 3.1 \text{ A}$

Typ. gate charge (P-Ch.)
 $V_{GS} = f(Q_{Gate})$

parameter: $I_D = -2 \text{ A}$


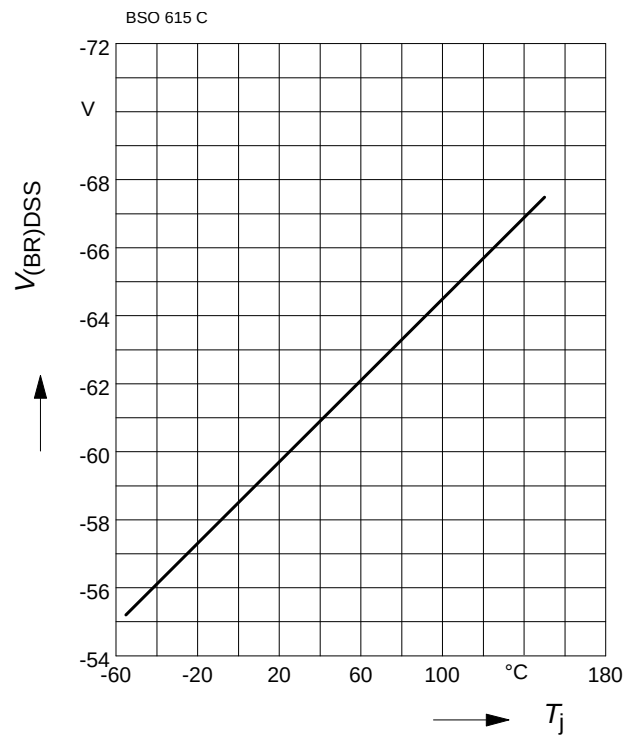
Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j), (N\text{-}Ch.)$$



Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j), (P\text{-}Ch.)$$



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